

Decreased Surface Photovoltage via Optimal Annealing Temperature for Enhanced Photoelectrochemical Performance of ZnO films

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(1) Typical contact potential difference mappings of different samples

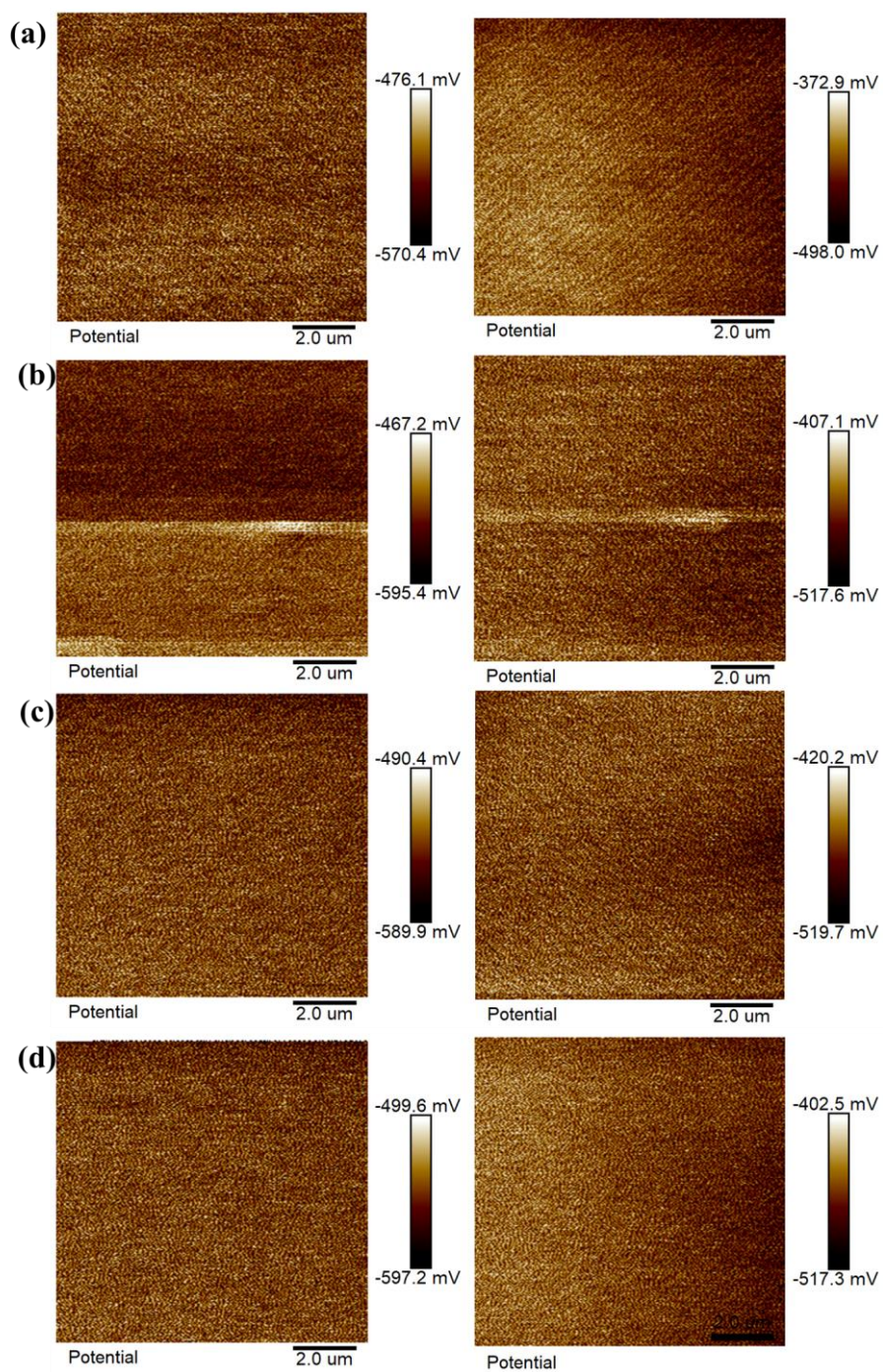


Figure S1. Contact potential difference in the dark (left) and under UV illumination (right) of various samples: (a) unannealed ZnO, (b) ZnO-350, (c) ZnO-450 and (d) ZnO-550.